

The Crystal Structure of β - Si_3N_4

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The crystal structure of β - Si_3N_4 is known from studies by Hardie and Jack¹, and Popper and Ruddlesden² with X-ray data obtained from powder photographs.

Although crystals of β - Si_3N_4 have been grown² by heating silicon in an ammonia atmosphere at 1500°C for three days, no single crystal structure investigation has been published.

A sample of crystals formed spontaneously on a ferrosilicon alloy in air at room temperature³ has been given us by Prof. K. Grjotheim. The sample contains both α - and β - Si_3N_4 .

The crystal structure of β - Si_3N_4 has been reinvestigated by us, using X-ray intensities measured photometrically from integrated Weissenberg films and corrected in the usual way. Needle-formed crystals of diameter about 30 μ were used for this investigation.

We have reaffirmed the space group $P6_3/m$ and unit cell parameters, $a = 7.607$ Å, $c = 2.911$ Å, found by the earlier investigators^{1,2}.

As the z -coordinates of all atoms are determined by the space group, only the $hk0$ -reflections have been utilized in this investigation.

Three cycles of least-squares refinement of the atomic coordinates were made, giving the final values for atoms in different special positions,

$$\begin{array}{lll} \text{N in } (c) & x = 1/2 & y = 2/3 & z = 1/4 \\ \text{N in } (h) & x = 0.321 & y = 0.025 & z = 1/4 \\ \text{Si in } (h) & x = 0.174 & y = -0.234 & z = 1/4 \end{array}$$

The coordinates of N in (h) are somewhat different from those of Hardie and Jack¹.

$$\begin{array}{lll} \text{N in } (h) & x = 0.333 & y = 0.033 & z = 1/4 \\ \text{Si in } (h) & x = 0.172 & y = -0.231 & z = 1/4 \end{array}$$

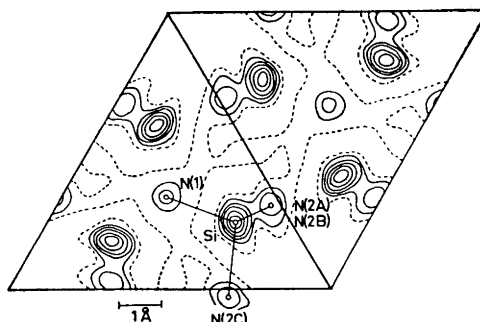


Fig. 1. Electron density projection of β - Si_3N_4 on (001).

The final reliability factor was $R = \Sigma |\Delta F| / \Sigma |F_0| = 0.109$.

An electron density projection on (001), calculated before the least-squares refinement, is shown in Fig. 1.

The interatomic distances within the distorted SiN_4 tetrahedron (see Fig. 1) are given below.

| | |
|-------------------------------|---------------------|
| Si - N(1) | 1.72 ₀ Å |
| Si - N(2A) = Si - N(2B) | 1.75 ₈ Å |
| Si - N(2C) | 1.71 ₁ Å |
| N(1) - N(2A) = N(1) - N(2B) | 2.89 ₃ Å |
| N(1) - N(2C) | 2.77 ₄ Å |
| N(2A) - N(2B) | 2.91 ₁ Å |
| N(2C) - N(2A) = N(2C) - N(2B) | 2.76 ₇ Å |

The standard deviations of the above distances are estimated to be less than 0.015 Å.

1. Hardie, D. and Jack, K. H. *Nature* **180** (1957) 332.
2. Ruddlesden, S. N. and Popper, P. *Acta Cryst.* **11** (1958) 465.
3. Grjotheim, K., Johnson, E. and Krohn, C. *Nature* **190** (1961) 23.

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